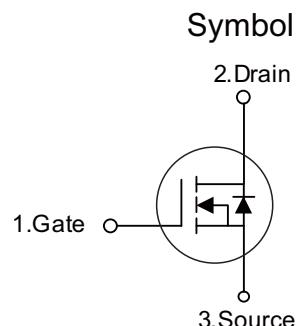


■ PRODUCT CHARACTERISTICS

VDSS	600V
R _{DS(on)Typ} (@V _{GS} = 10 V)	0.57Ω
Qg@type	38nC
ID	12A

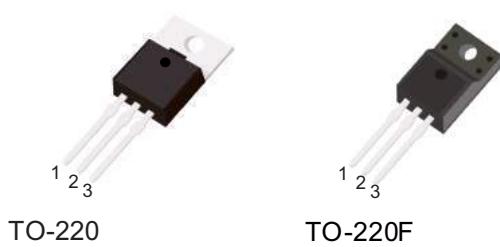


■ APPLICATIONS

- * High efficiency switch mode power supplies
- * Electronic lamp ballasts based on half bridge
- * LED power supplies

■ FEATURES

- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness



■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT12N60F	TO-220F	50 pieces/Tube
N/A	MOT12N60A	TO-220	50 pieces/Tube

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	600	V
Gate-Source Voltage		V _{GSS}	±30	V
Drain Current	Continuous	I _D	12	A
	Pulsed (Note 2)	I _{DM}	48	A
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	480	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.78	V/ns
Power Dissipation	TO-220	P _D	225	W
	TO-220F		51	W
Junction Temperature		T _J	+150	°C
Operating Temperature		T _{OPR}	-55 ~ +150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature

3. L = 5.8mH, I_{AS} = 12A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C

4. I_{SD} ≤ 12A, di/dt ≤ 200A/s, V_{DD} ≤ BV_{DSS} Starting T_J = 25°C

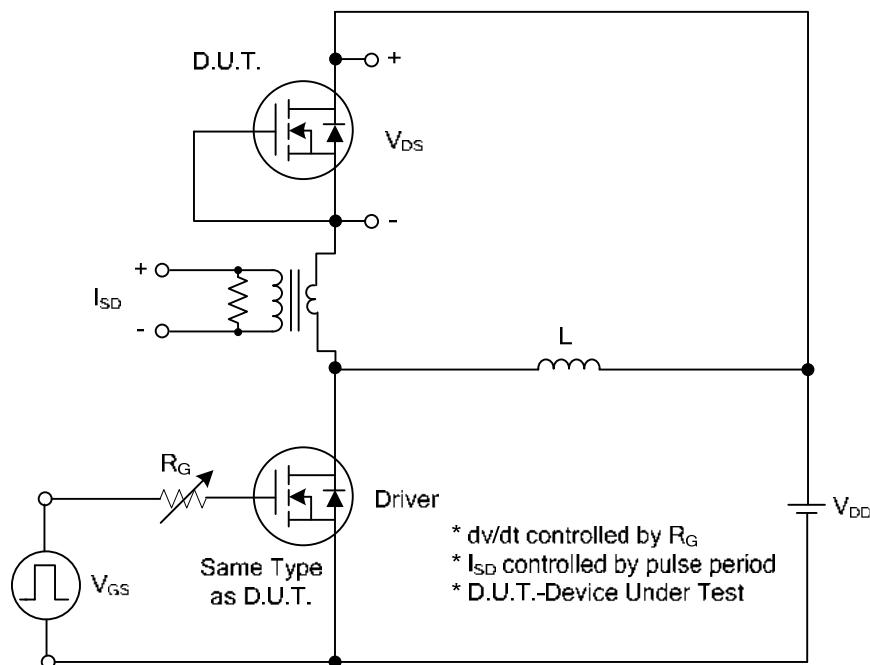
■ ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Off characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_D=250\mu\text{A}$	600	-	-	V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=600\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm30\text{V}, V_{\text{DS}}=0\text{V}$	-	-	±100	nA
Breakdown Voltage Temperature Coefficient	$\triangle \text{BV}_{\text{DSS}}/\triangle T_J$	$I_D=250\mu\text{A}$, Referenced to 25°C	-	0.7	-	$\text{V}/^\circ\text{C}$
On characteristics						
Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{DS}}=V_{\text{GS}}, I_D=250\mu\text{A}$	2.0	-	4.0	V
Static Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_D=6.0\text{A}$	-	0.57	0.70	Ω
Dynamic characteristics						
Input Capacitance	C_{ISS}	$V_{\text{DS}}=25\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$	-	1880	-	pF
Output Capacitance	C_{OSS}		-	180	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	10	-	pF
Switching characteristics						
Total Gate Charge	Q_G	$V_{\text{DS}}=300\text{V}, I_D=12\text{A}, V_{\text{GS}}=10\text{V}$ $I_G=1\text{mA}$ (Note1,2)	-	38	-	nC
Gate-Source Charge	Q_{GS}		-	13	-	nC
Gate-Drain Charge	Q_{GD}		-	8	-	nC
Turn-On Delay Time	$t_{\text{D}(\text{ON})}$	$V_{\text{DD}}=30\text{V}, I_D=0.5\text{A}, R_G=25\Omega$ (Note1,2)	-	90	-	ns
Turn-On Rise Time	t_R		-	109	-	ns
Turn-Off Delay Time	$t_{\text{D}(\text{OFF})}$		-	190	-	ns
Turn-Off Fall Time	t_F		-	100	-	ns
Source-drain diode ratings and characteristics						
Maximum Continuous Drain-Source Diode Forward Current	I_S	$V_{\text{GS}}=0\text{V}, I_S=12\text{A}$	-	-	12	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}		-	-	48	A
Drain-Source Diode Forward Voltage	V_{SD}	$V_{\text{GS}}=0\text{V}, I_S=12\text{A}$	-	-	1.4	V
Reverse Recovery Time	t_{rr}	$V_{\text{GS}}=0\text{V}, I_S=0.2\text{A},$ $dI/dt=100\text{A}/\mu\text{s}$	-	544	-	ns
Reverse Recovery Charge	Q_{rr}		-	5.9	-	μC

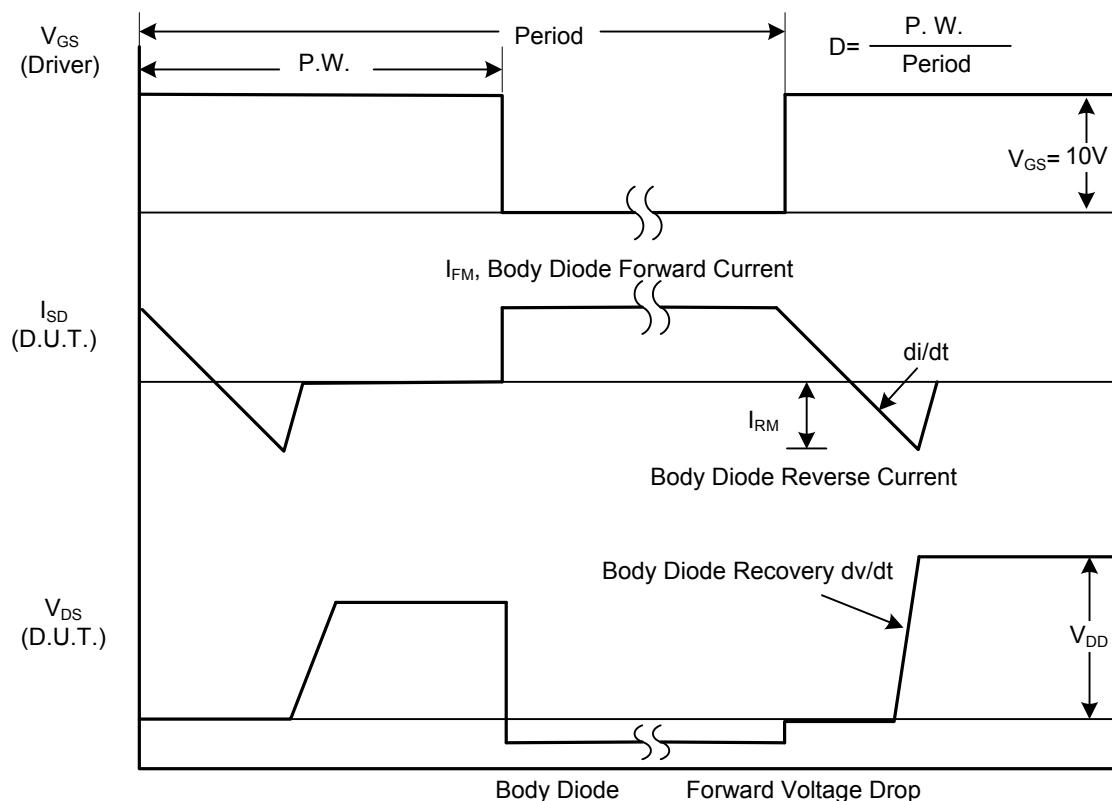
Notes: 1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

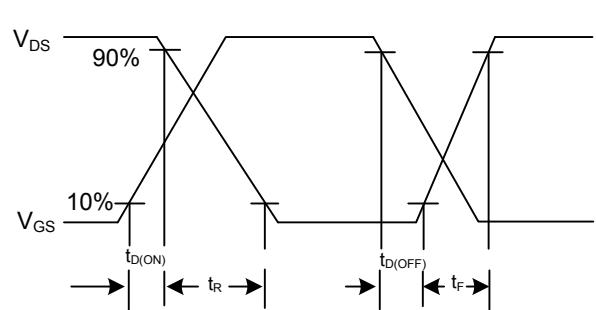
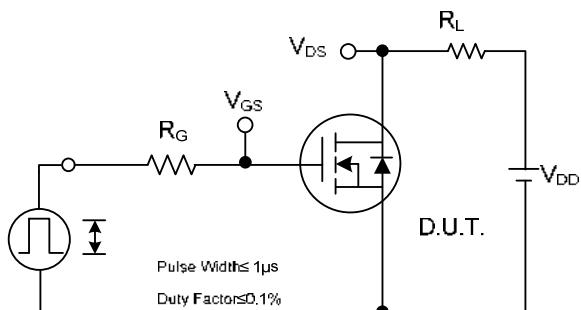
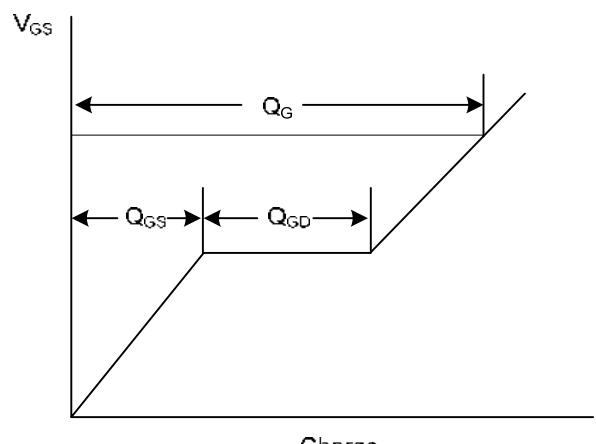
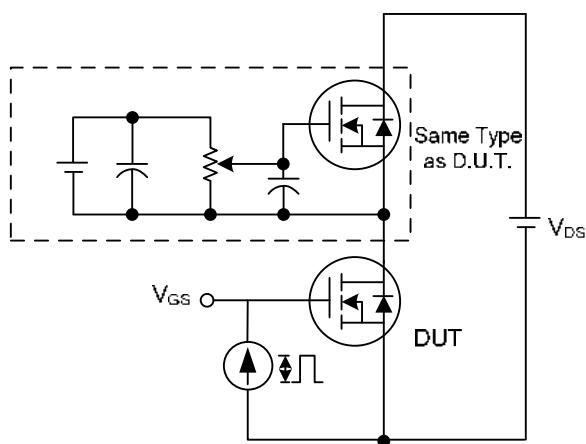
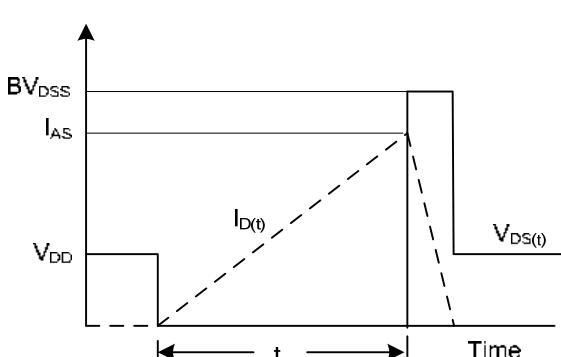
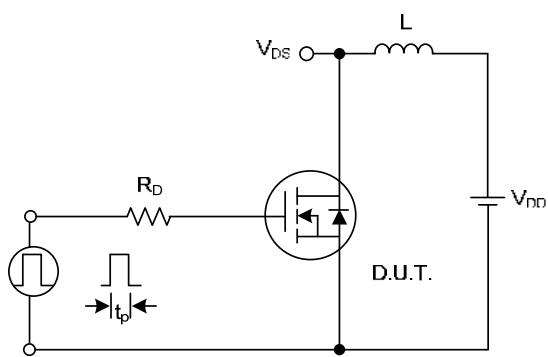


Peak Diode Recovery dv/dt Test Circuit

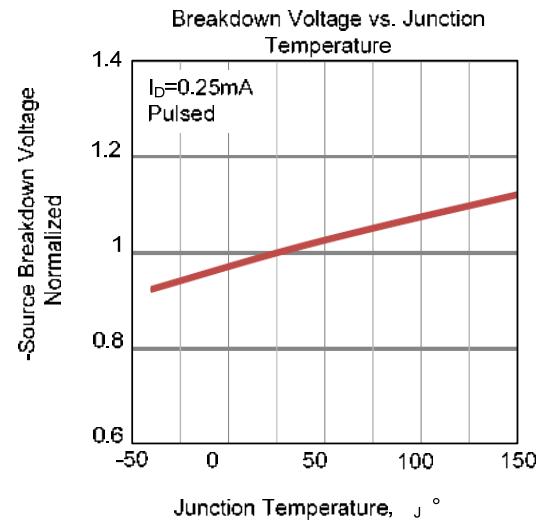
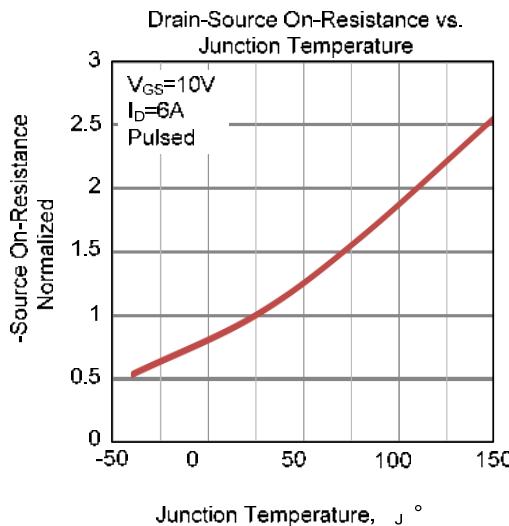
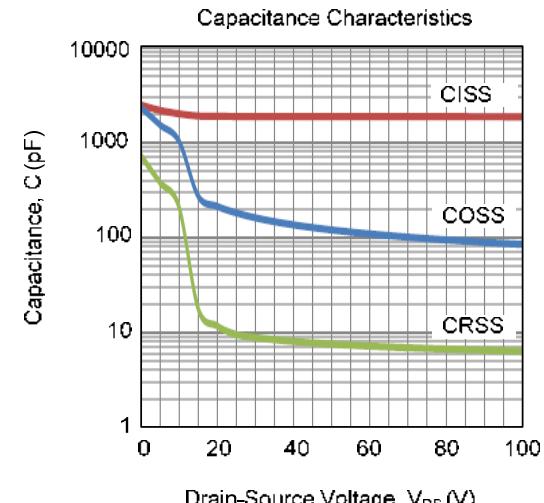
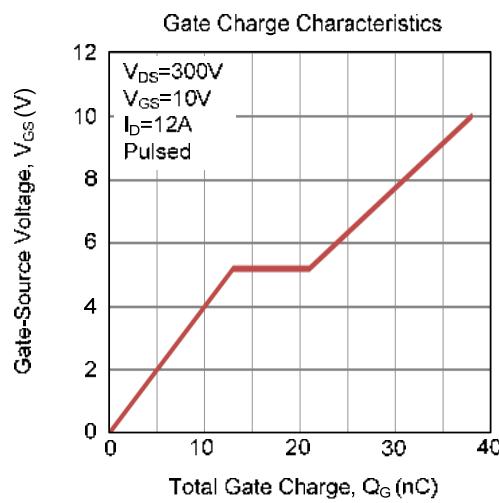
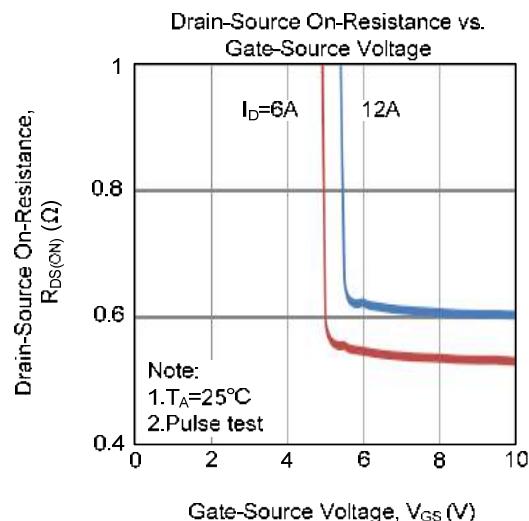
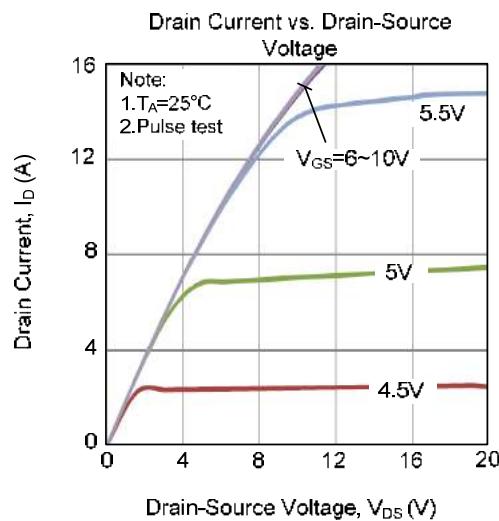


Peak Diode Recovery dv/dt Waveforms

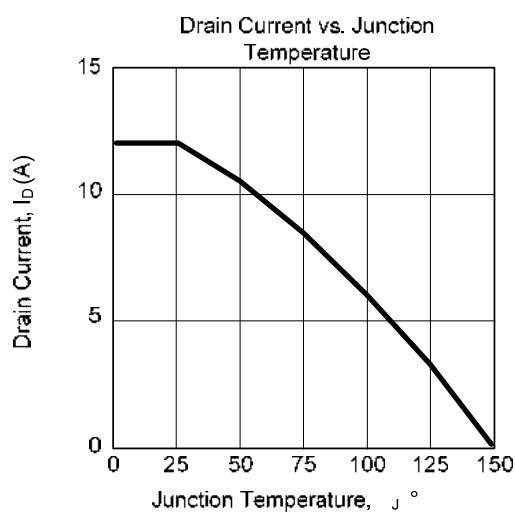
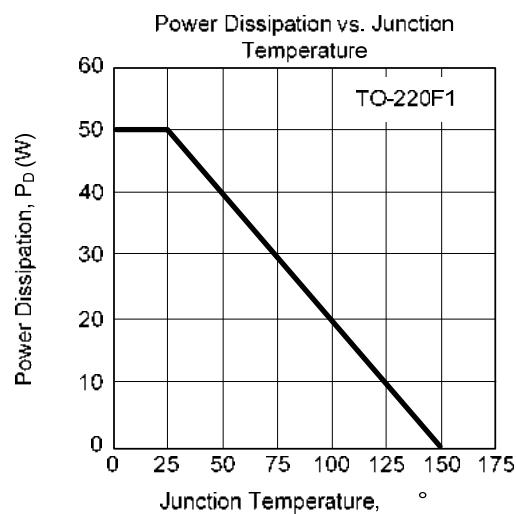
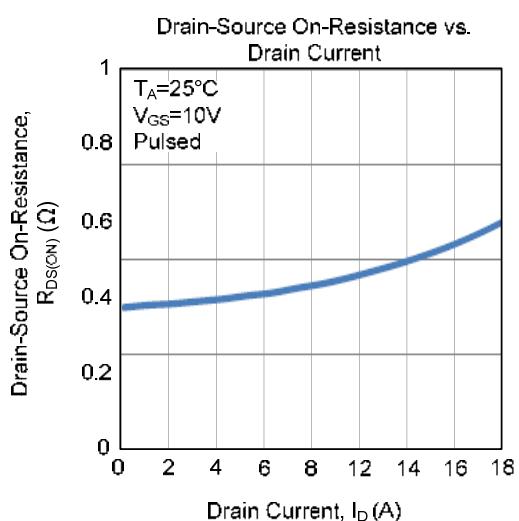
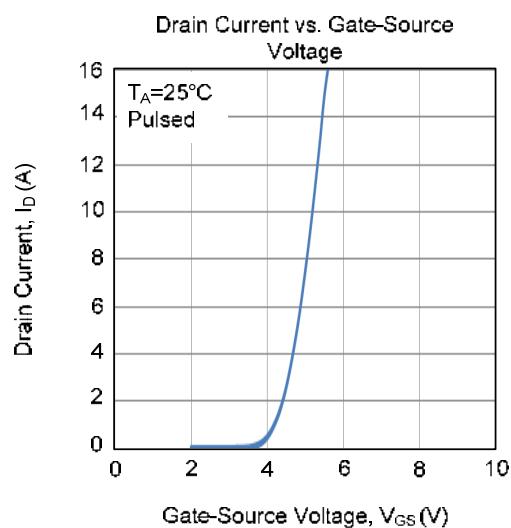
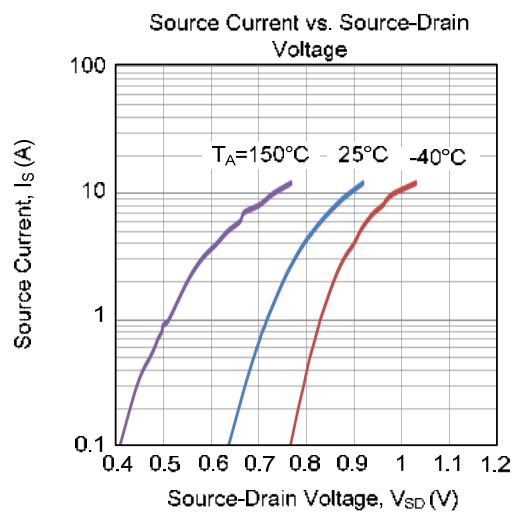
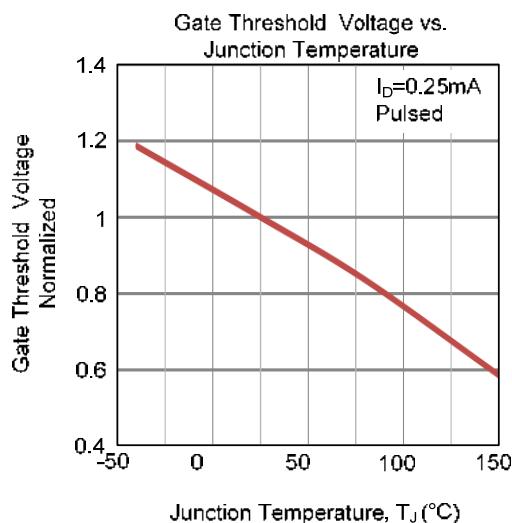
■ TEST CIRCUITS AND WAVEFORMS(Cont.)


Switching Test Circuit
Switching Waveforms

Gate Charge Test Circuit
Gate Charge Waveform

Unclamped Inductive Switching Test Circuit
Unclamped Inductive Switching Waveforms

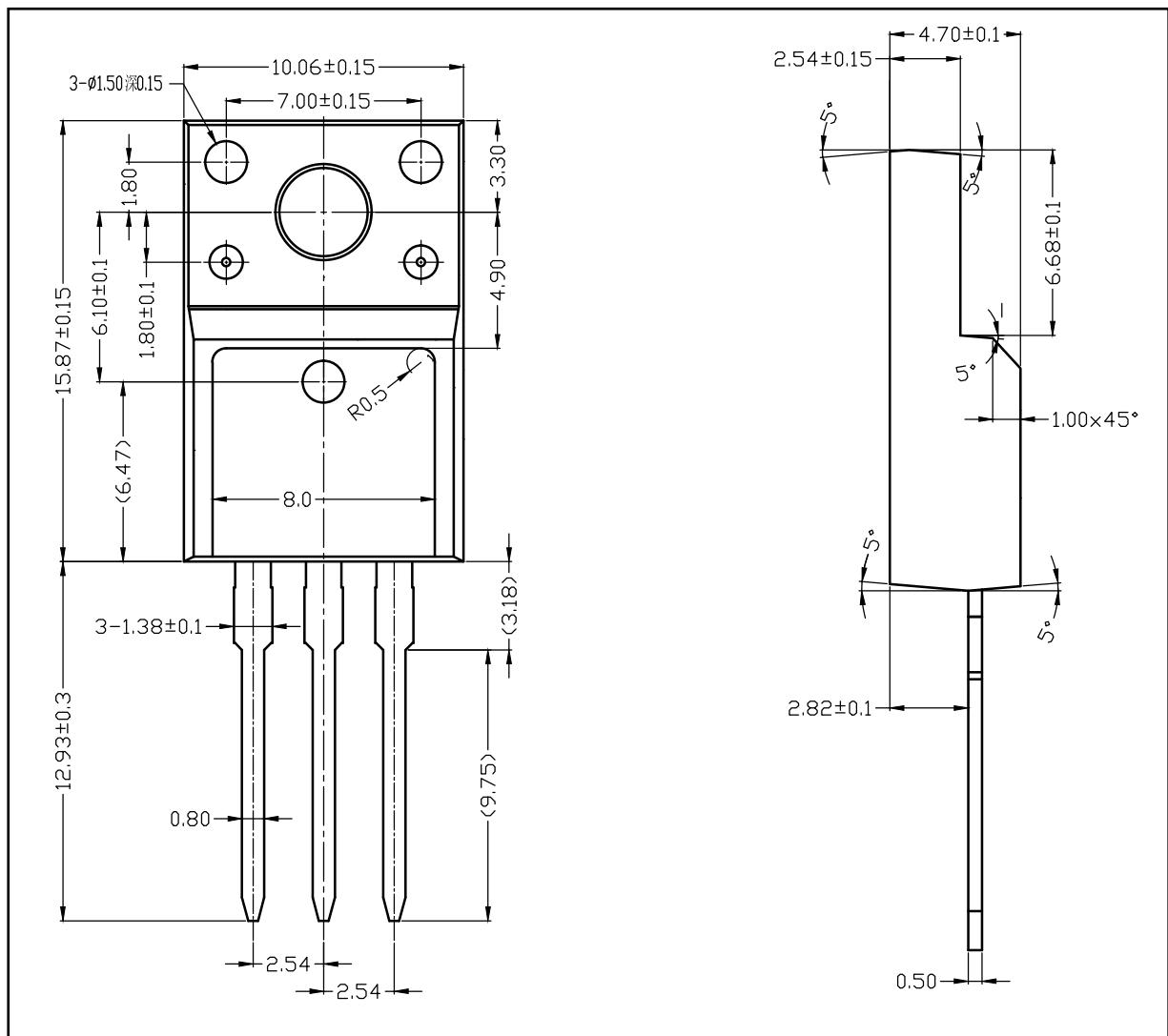
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)



■ TO-220F-3L PACKAGE OUTLINE DIMENSIONS





仁懋电子

MOT12N60A
MOT12N60F
N-CHANNEL MOSFET

■ TO-220-3L PACKAGE OUTLINE DIMENSIONS

